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November 2013

FDP33N25

N-Channel UniFETTM MOSFET 250 V, 33 A, 94 m Ω

Features

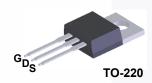
- $R_{DS(on)}$ = 94 $m\Omega$ (Max.) @ V_{GS} = 10 V, I_D = 16.5 A
- Low Gate Charge (Typ. 36.8 nC)
- Low C_{rss} (Typ. 39 pF)
- · 100% Avalanche Tested

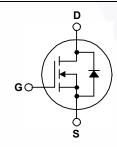
Applications

- PDP TV
- Lighting
- · Uninterruptible Power Supply
- AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter	FDP33N25	Unit
V_{DSS}	Drain-Source Voltage	250	V	
I _D	Drain Current	- Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	33 20.4	A
I _{DM}	Drain Current	- Pulsed (Note 1)	132	Α
V _{GSS}	Gate-Source voltage	± 30	V	
E _{AS}	Single Pulsed Avalan	nche Energy (Note 2)	918	mJ
I _{AR}	Avalanche Current	(Note 1)	33	Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		23.5	mJ
dv/dt	Peak Diode Recovery	y dv/dt (Note 3)	4.5	V/ns
P_D	Power Dissipation	(T _C = 25°C) - Derate Above 25°C	235 1.89	W/°C
T _{J,} T _{STG}	Operating and Stora	ge Temperature Range	-55 to +150	°C
T _L	Maximum Lead Temp	perature for Soldering, 1/8" from Case for 5 Seconds	300	°C

Thermal Characteristics

Symbol	Parameter	FDP33N25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.53	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	C/VV

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Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP33N25	FDP33N25	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25$ °C unless otherwise noted.

Symbol	Parameter	Conditions		Тур	Max	Unit
Off Charac	cteristics			•		
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}, T_J = 25^{\circ}\text{C}$				V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.25		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 250 V, V _{GS} = 0 V V _{DS} = 200 V, T _C = 125°C			1 10	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Charac	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 16.5 A		0.077	0.094	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 16.5 A		26.6		S
Dynamic C	Characteristics			•		
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		1640	2135	pF
C _{oss}	Output Capacitance			330	430	pF
C _{rss}	Reverse Transfer Capacitance			39	59	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	V_{DD} = 125 V, I_{D} = 33 A, V_{GS} = 10 V, R_{G} = 25 Ω (Note 4)		35	80	ns
t _r	Turn-On Rise Time			230	470	ns
t _{d(off)}	Turn-Off Delay Time			75	160	ns
t _f	Turn-Off Fall Time			120	250	ns
Q _g	Total Gate Charge	V _{DS} = 200 V, I _D = 33 A,		36.8	48	nC
Q _{gs}	Gate-Source Charge			10		nC
Q _{gd}	Gate-Drain Charge			17		nC
Drain-Sou	rce Diode Characteristics and Maximur	n Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				33	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				132	Α
V_{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 33 A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 33 A,		220		ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt =100 A/μs		1.71		μС

Notes

^{1.} Repetitive rating: pulse-width limited by maximum junction temperature.

^{2.} L = 1.35 mH, I_{AS} = 33 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.

^{3.} I $_{SD} \leq$ 33 A, di/dt \leq 200 A/µs, V $_{DD} \leq$ BV $_{DSS},$ starting T $_{J}$ = 25°C.

^{4.} Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

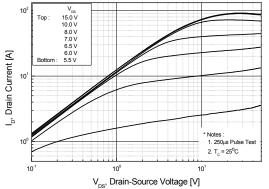
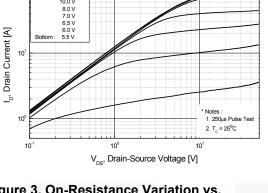


Figure 3. On-Resistance Variation vs. **Drain Current and Gate Voltage**

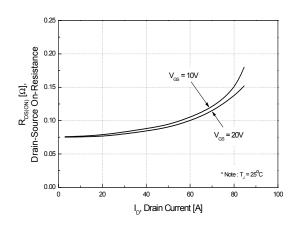


Notes : 1. V_{DS} = 40V 2. 250µs Pulse Tes $V_{\rm GS}$, Gate-Source Voltage [V]

Figure 2. Transfer Characteristics

_{lo}, Drain Current [A]

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue



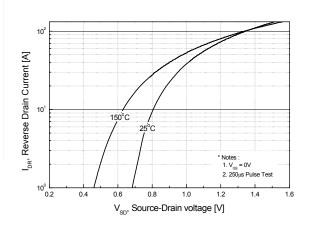


Figure 5. Capacitance Characteristics

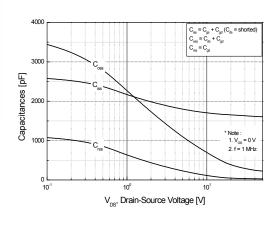
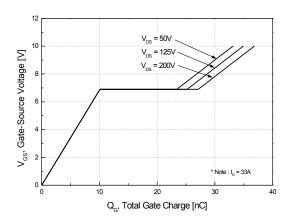


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

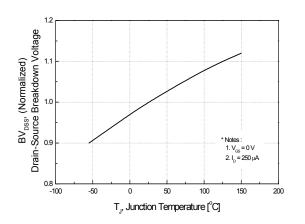


Figure 8. On-Resistance Variation vs. Temperature

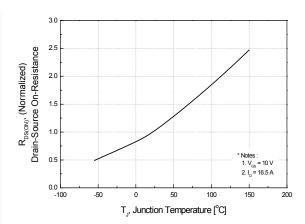


Figure 9. Maximum Safe Operating Area

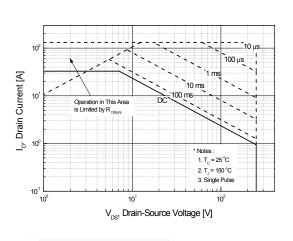


Figure 10. Maximum Drain Current vs. Case Temperature

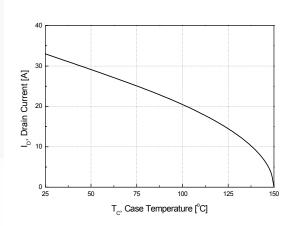
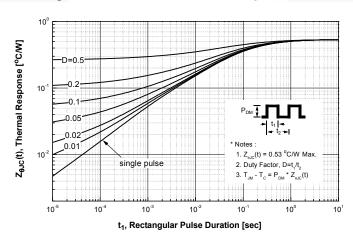


Figure 11. Transient Thermal Response Curve



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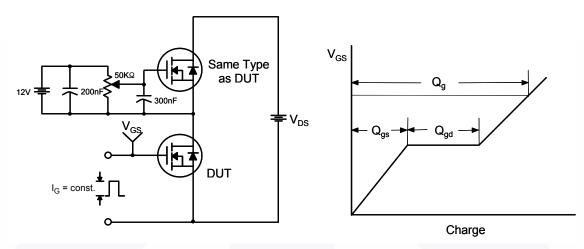


Figure 12. Gate Charge Test Circuit & Waveform

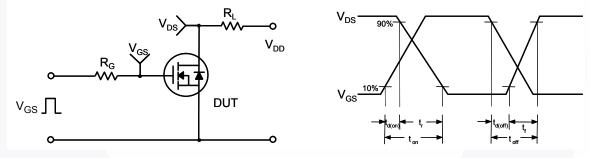


Figure 13. Resistive Switching Test Circuit & Waveforms

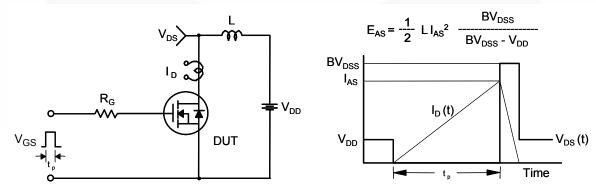


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

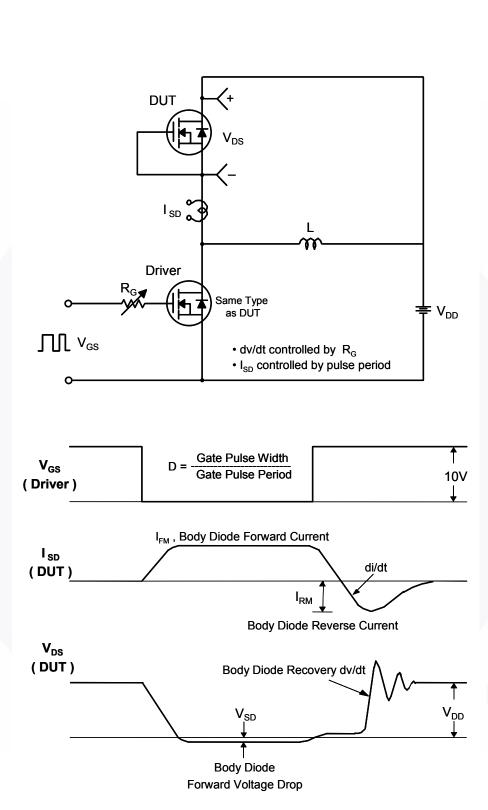


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

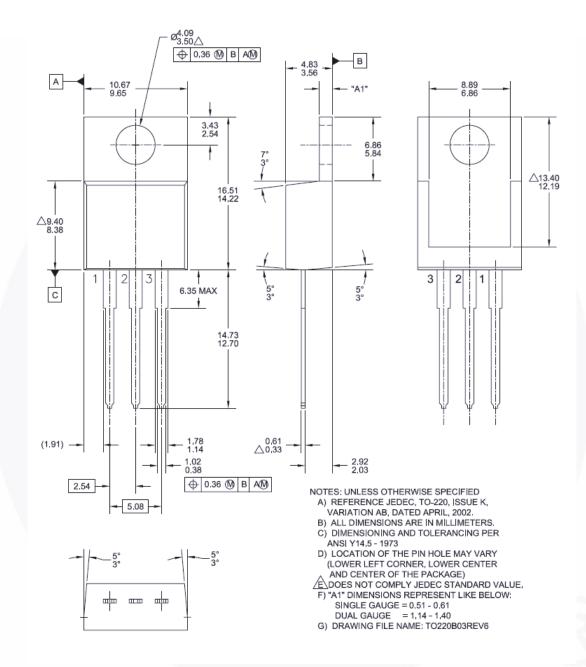


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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